

**SCOPE: CMOS, BUFFERED, MULTIPLYING 8-BIT D/A CONVERTER**

<u>Device Type</u>	<u>Generic Number</u>	<u>Circuit Function</u>
01	MX7528S(x)/883B	DAC with $\pm 4$ LSB
02	MX7528T(x)/883B	DAC with $\pm 2$ LSB
03	MX7528U(x)/883B	DAC with $\pm 1$ LSB

**Case Outline(s).** The case outlines shall be designated in Mil-Std-1835 and as follows:

<u>Outline Letter</u>	<u>Mil-Std-1835</u>	<u>Case Outline</u>	<u>Package Code</u>
MAXIM SMD			
Q R	GDIP1-T20 or CDIP2-T20	20 LEAD CERDIP	J20

**Absolute Maximum Ratings:**

$V_{DD}$ to AGND .....	0V, +17V
$V_{DD}$ to DGND .....	0V, +17V
$V_{RFBA}$ , $V_{RFBB}$ to DGND .....	$\pm 25$ V
$V_{REFA}$ , $V_{REFB}$ to AGND .....	$\pm 25$ V
Digital Input Voltage to DGND .....	-0.3V to $V_{DD}+0.3$ V
V pin 1 to DGND .....	-0.3V to $V_{DD}$
V pin 2, V pin 20 to AGND .....	-0.3V to $V_{DD}+0.3$ V
AGND to DGND .....	-0.3V, $V_{DD}+0.3$ V
DGND to AGND .....	+0.3V
Lead Temperature (soldering, 10 seconds) .....	+300°C
Storage Temperature .....	-65°C to +150°C

Continuous Power Dissipation .....	$T_A=+70^\circ\text{C}$
20 pin CERDIP(derate 11.1mW/°C above +70°C) .....	889mW

Junction Temperature $T_J$ .....	+150°C
Thermal Resistance, Junction to Case, $\theta_{JC}$	
20 pin CERDIP.....	40°C/W
Thermal Resistance, Junction to Ambient, $\theta_{JA}$ :	
20 pin CERDIP.....	90°C/W

**Recommended Operating Conditions**

Ambient Operating Range ( $T_A$ ) .....	-55°C to +125°C
Supply Voltage Range ( $V_{DD}$ ) .....	+4.75V to +5.25V and +14.25V to +15.75V
$V_{REF}$ DAC A = $V_{REF}$ DAC B .....	+10V
OUT DAC A = OUT DAC B .....	0V

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TABLE 1. ELECTRICAL TESTS:**

TEST	Symbol	CONDITIONS	Group A Subgroup	Device type	Limits Min	Limits Max	Units
		-55 °C ≤ T <sub>A</sub> ≤ +125 °C <u>1</u> / Unless otherwise specified					
<b>ACCURACY</b>							
Resolution NOTE 4	RES	V <sub>DD</sub> =+5V and V <sub>DD</sub> =+15V	1,2,3	All	8.0		Bits
Relative Accuracy	RA	V <sub>DD</sub> =+5V and V <sub>DD</sub> =+15V	1,2,3	01		±1.0	LSB
Relative Accuracy	RA	V <sub>DD</sub> =+5V and V <sub>DD</sub> =+15V	1 2,3	02,03		±1.0 ±0.5	LSB
Relative Accuracy	RA	V <sub>DD</sub> =+5V & V <sub>DD</sub> =+15V, NOTE 2	12	02,03		±0.5	LSB
Differential Nonlinearity	DNL	V <sub>DD</sub> =+5V and V <sub>DD</sub> =+15V Monotonic to 8-Bits	1,2,3	All		±1.0	LSB
Gain Error NOTE 3	AE	V <sub>DD</sub> =+5V and V <sub>DD</sub> =+15V	1	All		±4.0	LSB
Gain Error NOTE 3	AE	V <sub>DD</sub> =+5V V <sub>DD</sub> =+15V	2,3	01		±6.0 ±5.0	LSB
Gain Error NOTE 2,3	AE	V <sub>DD</sub> =+5V V <sub>DD</sub> =+15V	2,3	02		±4.0 ±3.0	LSB
		V <sub>DD</sub> =+5V V <sub>DD</sub> =+15V	12			±2.0 ±1.0	
Gain Error NOTE 2,3	AE	V <sub>DD</sub> =+5V V <sub>DD</sub> =+15V	2,3	03		±3.0 ±1.0	LSB
		V <sub>DD</sub> =+5V, V <sub>DD</sub> =+15V	12			±1.0	
Power Supply Rejection	PSRR	V <sub>DD</sub> =+5V, ΔV <sub>DD</sub> =±5%	1 2,3	All		±0.02 ±0.04	%/%
Power Supply Rejection	PSRR	V <sub>DD</sub> =+15V, ΔV <sub>DD</sub> =±5%	1 2,3	All		±0.01 ±0.02	%/%
Output Leakage Current PIN 2 and 20	I <sub>OL</sub>	V <sub>DD</sub> =+5V, DAC latches loaded with 0000 0000	1 2,3	All		±50 ±400	nA
Output Leakage Current PIN 2 and 20	I <sub>OL</sub>	V <sub>DD</sub> =+15V, DAC latches loaded with 0000 0000	1 2,3	All		±50 ±200	nA
Reference Input Resistance V <sub>REF</sub> A, V <sub>REF</sub> B	R <sub>IN</sub>	V <sub>DD</sub> =+5V and +15V	1,2,3	All	8	15	kΩ
Digital Input High Voltage	V <sub>IH</sub>	V <sub>DD</sub> =+5V V <sub>DD</sub> =+15V	1,2,3	All	2.4 13.5		V
Digital Input Low Voltage	V <sub>IL</sub>	V <sub>DD</sub> =+5V V <sub>DD</sub> =+15V	1,2,3	All		0.8 1.5	V
Digital Input Leakage Current	I <sub>IN</sub>	V <sub>DD</sub> =+5V V <sub>IN</sub> =0V or V <sub>DD</sub>	1 2,3	All		±1.0 ±10	μA
Digital Input Leakage Current	I <sub>IN</sub>	V <sub>DD</sub> =+15V V <sub>IN</sub> =0V or V <sub>DD</sub>	1 2,3	All		±1.0 ±10	μA
Supply Current	I <sub>DD</sub>	V <sub>DD</sub> =+5V All digital inputs V <sub>DD</sub> =+15V V <sub>IL</sub> or V <sub>IH</sub>	1,2,3	All		2.0 2.0	mA
Supply Current	I <sub>DD</sub>	V <sub>DD</sub> =+5V & +15V. All digital inputs 0V or V <sub>DD</sub>	1 2,3	All		100 500	μA
Gain Temperature Coefficient NOTE 4	TC <sub>AE</sub>	V <sub>DD</sub> =+5V V <sub>DD</sub> =+15V	1,2,3	All		±70 ±35	ppm/°C

TEST	Symbol	CONDITIONS		Group A Subgroup	Device type	Limits Min	Limits Max	Units
		-55 °C <=T <sub>A</sub> <= +125°C 1/ Unless otherwise specified						
Feedthrough Error V <sub>REFA</sub> to OUTA and V <sub>REFB</sub> to OUTB	FT <sub>REFA</sub>	V <sub>DD</sub> =+5V or V <sub>DD</sub> =+15V, V <sub>REF</sub> =+10V, 100kHz sinewave, DAC latches loaded with 0000 0000 NOTE 4, NOTE 5		4,5,6	All		-70	dB
Digital Input Capacitance NOTE 6	C <sub>IN</sub>	V <sub>DD</sub> =+5V DB0-DB7 V <sub>DD</sub> =+15V		4	All		10 20	pF
Digital Input Capacitance NOTE 6	C <sub>IN</sub>	V <sub>DD</sub> =+5V _____ WR, CS, DACA/DACB V <sub>DD</sub> =+15V		4	All		10 15	pF
<b>ANALOG INPUTS</b>								
Digital Output pin 2 Capacitance 6/ pin 20	C <sub>OUTA</sub> C <sub>OUTB</sub>	V <sub>DD</sub> =+5V and 15V, DAC latches loaded with 0000 0000		4	All		50 50	pF
Digital Output pin 2 Capacitance 6/ pin 20	C <sub>OUTA</sub> C <sub>OUTB</sub>	V <sub>DD</sub> =+5V and 15V, DAC latches loaded with 1111 1111		4	All		120 120	pF
<b>TIMING</b>								
Chip select to write setup time NOTE 7	t <sub>CS</sub>	V <sub>DD</sub> =+5V  V <sub>DD</sub> =+15V		9 10,11  9 10,11	All	200 230  60 80		ns
Chip select to write hold time NOTE 7	t <sub>CH</sub>	V <sub>DD</sub> =+5V  V <sub>DD</sub> =+15V		9 10,11  9 10,11	All	20 30  10 15		ns
Write pulse width NOTE 7	t <sub>WR</sub>	V <sub>DD</sub> =+5V, t <sub>CS</sub> ≥t <sub>WR</sub> , t <sub>CH</sub> ≥0  V <sub>DD</sub> =+15V, t <sub>CS</sub> ≥t <sub>WR</sub> , t <sub>CH</sub> ≥0		9 10,11  9 10,11	All	180 200  60 80		ns
Data valid to write setup time NOTE 7	t <sub>DS</sub>	V <sub>DD</sub> =+5V  V <sub>DD</sub> =+15V		9 10,11  9 10,11	All	110 130  50 70		ns
Data valid to write hold time NOTE 7	t <sub>DH</sub>	V <sub>DD</sub> =+5V  V <sub>DD</sub> =+15V		9,10,11	All	10 10		ns
Data select to write setup time NOTE 7	t <sub>AS</sub>	V <sub>DD</sub> =+5V  V <sub>DD</sub> =+15V		9 10,11  9 10,11	All	200 230  60 80		ns

TEST	Symbol	CONDITIONS		Limits Min	Limits Max	Units
		-55 °C ≤ T <sub>A</sub> ≤ +125°C, <u>1</u> / Unless otherwise specified	Group A Subgroup			
Data select to write hold time NOTE 7	t <sub>AH</sub>	V <sub>DD</sub> =+5V  V <sub>DD</sub> =+15V	9 10,11  9 10,11	All	20 30  10 15	ns
Reference input resistance match	<u>R</u> MIN ΔV <sub>REF</sub>	V <sub>DD</sub> =+5V  V <sub>DD</sub> =+15V	4,5,6	All	±1  ±1	%
Channel to Channel isolation NOTE 4 V <sub>REF</sub> A to OUTB	CHISO	V <sub>DD</sub> =+5V or +15V. V <sub>REF</sub> A=±10V, 100kHz sinewave, V <sub>REF</sub> B=0V	4,5,6	All	-60	dB
Channel to Channel isolation NOTE 4 V <sub>REF</sub> B to OUTA	CHISO	V <sub>DD</sub> =+5V or +15V. V <sub>REF</sub> B=±10V, 100kHz sinewave, DAC, V <sub>REF</sub> A=0V	4,5,6	All	-60	dB
Output Current Settling Time NOTE 4	t <sub>SL</sub>	V <sub>DD</sub> =+5V  V <sub>DD</sub> =+15V	9,10,11	All	350  180	ns

NOTE 1: V<sub>OUT1</sub>=0V; V<sub>REF</sub>=+10V, AGND=DGND unless otherwise specified.

NOTE 2: Optional Subgroup 12 is used for grading and part selection at +25°C.

NOTE 3: Measured using internal RFBA and RFBB. Gain error is adjustable. DAC register loaded with 1111, 1111, 1111.

NOTE 4: Guaranteed, if not tested.

NOTE 5: Feedthrough error can be reduced by connecting the metal lid to ground.

NOTE 6: Subgroup 4 (C<sub>IN</sub> and C<sub>OUT</sub> measurements) shall be measured only for the initial test and after process or design changes which may affect capacitance.

NOTE 7: Timing in accordance with Write Cycle Timing Diagram in Commercial Data Sheet.

#### MODE SELECTION TABLE:

<u>CS</u>	<u>WR</u>	<u>DAC A/DAC B</u>	DAC A	DAC B
L	L	L	Write	Hold
L	L	H	Hold	Write
H	X	X	Hold	Hold
X	H	X	Hold	Hold

L = Low state, H = High state, X = Don't care

#### TERMINAL CONNECTIONS:

Pin		Pin	
1	AGND	11	DB3
2	OUTA	12	DB2
3	RFBA	13	DB1
4	VREFA	14	DB0(LSB)
5	DGND	15	<u>CS</u>
6	<u>DAC A/DAC B</u>	16	<u>WR</u>
7	(MSB)DB7	17	VDD
8	DB6	18	VREFB
9	DB5	19	RFBB
10	DB4	20	OUTB

**ORDERING INFORMATION:**

	Package	Pkg. Code	Device ID	SMD Number
01	20 pin CERDIP	J20	MX7528SQ/883B	5962-8770101RA
02	20 pin CERDIP	J20	MX7528TQ/883B	5962-8770102RA
03	20 pin CERDIP	J20	MX7528UQ/883B	5962-8770103RA

**QUALITY ASSURANCE**

Sampling and inspection procedures shall be in accordance with MIL-Prf-38535, Appendix A as specified in Mil-Std-883.

Screening shall be in accordance with Method 5004 of Mil-Std-883. Burn-in test Method 1015:

1. Test Condition, A, B, C, or D.
2. TA = +125°C minimum.
3. Interim and final electrical test requirements shall be specified in Table 2.

Quality conformance inspection shall be in accordance with Method 5005 of Mil-Std-883, including Groups A, B, C, and D inspection.

Group A inspection:

1. Tests as specified in Table 2.
2. Selected subgroups in Table 1, Method 5005 of Mil-Std-883 shall be omitted.

Group C and D inspections:

- a. End-point electrical parameters shall be specified in Table 1.
- b. Steady-state life test, Method 1005 of Mil-Std-883:
  1. Test condition A, B, C, D.
  2. TA = +125°C, minimum.
  3. Test duration, 1000 hours, except as permitted by Method 1005 of Mil-Std-883.

**TABLE 2. ELECTRICAL TEST REQUIREMENTS**

Mil-Std-883 Test Requirements	Subgroups per Method 5005, Table 1
Interim Electric Parameters Method 5004	1
Final Electrical Parameters Method 5005	1*, 2, 3, 12
Group A Test Requirements Method 5005	1, 2, 3, 4, 5, 6, 9, 10**, 11**, 12
Group C and D End-Point Electrical Parameters Method 5005	1

\* PDA applies to Subgroup 1 only.

\*\* Subgroups 10 and 11, if not tested shall be guaranteed to the limits specified in Table 1.